

Interaction of point defects with impurities in the Si-SiO₂ system and its influence on the interface properties
Kropman, Daniel; Mellikov, Enn; Kärner, Tiit; Heinmaa, Ivo; Laas, Tõnu; Londos, Charalampos; Misiuk, Andrzej Solid state phenomena 2011 / p. 263-266

Stress relaxation mechanism by strain in the Si-SiO₂ system and its influence on the interface properties
Kropman, Daniel; Mellikov, Enn; Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262